
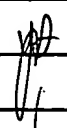




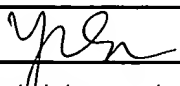


Form PTO-139		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1568		SERIAL NO. 09879,335	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Vishnu K. Agarwal, et al.		FILING DATE June 11, 2001	
				GROUP 2813			

U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
yke	AA	5,786,248	07/1998	Schuegraf			
	AB	3,571,914	03/1971	Lands, et al.			
	AC	4,464,701	08/1984	Roberts et al.			
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	AL	5,622,883	04/1997	Kim			
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
yke	AM	7611928	3/77	Netherlands			Yes No
	AN						X
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
yke	AQ		Kamiyama, Satoshi et al., "Ultrathin Tantalum Oxide Capacitor Dielectric Layers Fabricated Using Rapid Thermal Nitridation Prior to Low Pressure Chemical Vapor Deposition: J. Electrochem. Soc., Vol. 140, #6, pp 1618-25 (6/1993)				
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yke	AQ		Kamiyama, S., et al., Highly Reliable 2.5 nm Ta ₂ O ₅ Capacitor Process Technology for 256 Mbit DRAMs", IEEE, pp. 827-830 (9/1991)				
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EXAMINER				DATE CONSIDERED 3/18/02			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1568		SERIAL NO. 09/879,335	
		LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT Kunal R. Parekh, et al.		FILING DATE June 11, 2001	
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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	5,597,756 /	01/1997	Fazan et al.			
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FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
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	AO		Fazan, P.C., et. al., "A High-C Capacitor (20.4fF/μm ²) with Ultrathin CVD-Ta ₂ O ₅ Films Deposited on Rugged Poly-Si for High Density DRAMS", 1992 IEEE, pp. 263-266.				
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	AR						
EXAMINER 				DATE CONSIDERED 8/18/02			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							